

Designed for general-purpose amplifier and low speed switching applications.

High DC Current Gain -

 $h_{FE} = 3500 \text{ (Typ) } @ I_C = 4.0 \text{ Adc}$

Collector-Emitter Sustaining Voltage - @ 200 mAdc

 $V_{CEO(sus)} = 60 \text{ Vdc (Min)} - 2N6667$ = 80 Vdc (Min) - 2N6668

Low Collector-Emitter Saturation Voltage -

 $V_{CE(sat)} = 2.0 \text{ Vdc (Max)} @ I_C = 5.0 \text{ Adc}$

Monolithic Construction with Built-In Base-Emitter Shunt Resistors

TO-220AB Compact Package

Complementary to 2N6387, 2N6388

These Devices are Pb-Free and are RoHS Compliant*

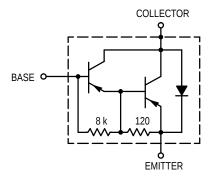
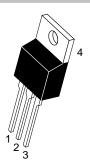


Figure 1. Darlington Schematic

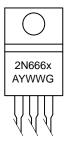
www.onsemi.com

PNP SILICON DARLINGTON POWER TRANSISTORS 10 A, 60–80 V, 65 W



TO-220 CASE 221A STYLE 1

MARKING DIAGRAM



x = 7 or 8

A = Assembly Location

Y = Year

WW = Work Week

G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
2N6667G	TO-220 (Pb-Free)	50 Units/Rail
2N6668G	TO-220 (Pb-Free)	50 Units/Rail

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



Symbol	2N6667	2N6668	Unit
V _{CEO}	60	80	Vdc
V_{CB}	60	80	Vdc
V_{EB}	5.0		Vdc
I _C	10 15		Adc
Ι _Β	250		mAdc

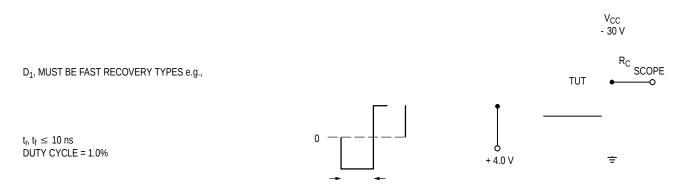


Figure 2. Switching Times Test Circuit

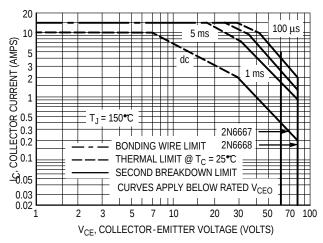
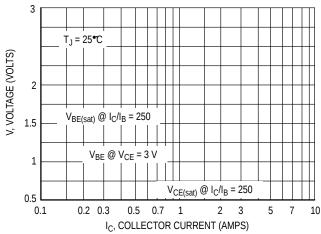


Figure 6. Maximum Safe Operating Area

2N6667, 2N6668





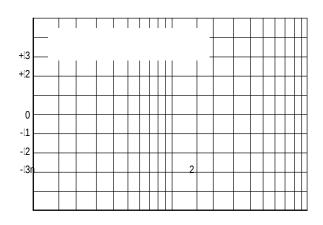


Figure 12. Typical Temperature Coefficients

